ΡΛΝ	JIT
	SEMI
	CONDUCTOR

40V N-Channel Enhancement Mode MOSFET

Voltage

90A Current

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@20A<5.5mΩ
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<7.5mΩ

40 V

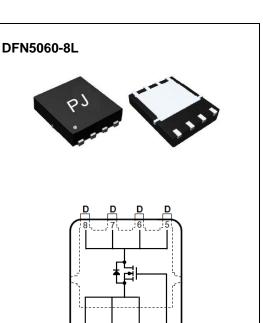
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0028 ounces, 0.08 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	1	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40		
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C		90		
	$T_{\rm C}=100^{\circ}{\rm C}$	I _D	57	А	
Pulsed Drain Current (Note 1)	T _c =25°C	I _{DM}	240		
Power Dissipation	T _c =25°C		99.3	14/	
	T _c =100°C	PD	49.7	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	14		
	T _A =70°C		11	A	
Power Dissipation	T _A =25°C	PD	2.4	14/	
	T _A =70°C		1.6	W	
Operating Junction and Storage 1	emperature Range	T _J ,T _{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	1.51		
	Junction to		00 5	°C/W	
	Ambient	R _{θJA}	62.5		





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1	1.7	2.5	V
Drain-Source On-State Resistance		V _{GS} =10V, I _D =20A	-	4.2	5.5	mΩ
	$R_{DS(on)}$	V _{GS} =4.5V, I _D =10A	-	5.3	7.5	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V _{DS} =32V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	25	-	nC
Gate-Source Charge	Q _{gs}		-	7	-	
Gate-Drain Charge	Q _{gd}		-	10	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	1258	-	pF
Output Capacitance	Coss		-	134	-	
Reverse Transfer Capacitance	Crss		-	88	-	
Turn-On Delay Time	td _(on)	V _{DS} =20V, I _D =1A, V _{GS} =10V, R _G =3.3Ω	-	18	-	
Turn-On Rise Time	t _r		-	13	-	
Turn-Off Delay Time	td _(off)		-	109	-	ns
Turn-Off Fall Time	t _f	(-	73	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					00	A
Diode Forward Current	I _S		-	-	90	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.7	1	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25$ °C.
- 4. The maximum current rating is package limited.
- 5. R_{®JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =38A, V_{DD} =25V, V_{GS} =10V, Starting T_{J} =25°C.
- 7. Guaranteed by design, not subject to production testing.

SEMI CONDUCTOR

PAN

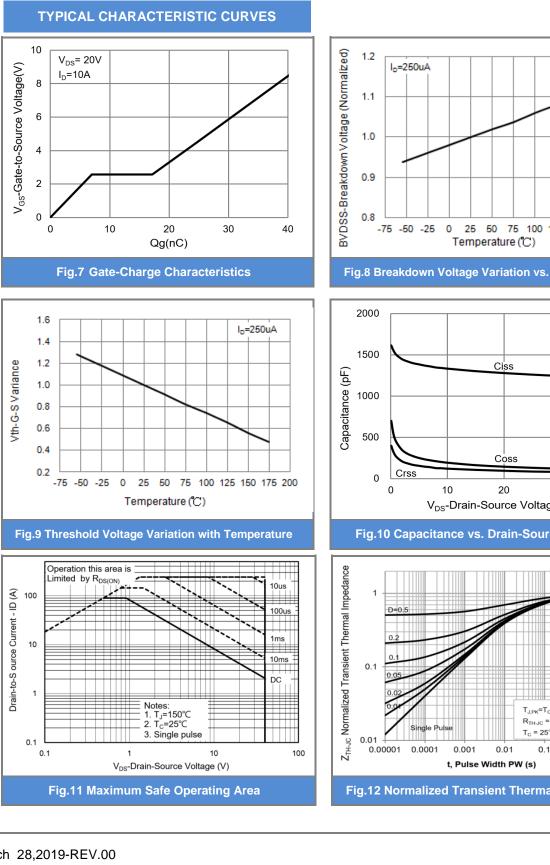


PJQ5442-AU TYPICAL CHARACTERISTIC CURVES 200 20 V_{GS}=10V,8V,6V,5V4.5V V_{DS}=5V I_{DS}-Drain-to-S ource Current(A) V_{GS}=4V I_{DS}-Drain-to-S ource Current(A) 150 15 V_{GS}=3.5V 100 10 V_{GS}=3V T_=125°C T_J=25°C 50 5 V_{GS}=2.5V 0 0 0 2 3 5 4 1 0 1 3 4 5 2 V_{DS}- Drain-to-Source Voltage(V) V_{GS}-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 8 2.5 Ros(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m Ω) 2.0 7 V_{GS}= 4.5V V_{G8}=10V, I_D=20A 1.5 6 1.0 Vge=4.5V, Ip=10A 5 0.5 V_{GS}= 10V 4 0.0 -75 -50 -25 0 25 50 75 100 125 150 175 200 0 5 10 15 20 Temperature (°C) I_{DS}-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 20 I_D=10A 10 I_{sD}-Source to Drain Current(A) $R_{DS}(on)$ - On-Resistance(m Ω) 15 1 10 T_i=125℃ т_ј=25°С T_i=125°C 0.1 T₁=25°C 5 0 0.01 2 4 6 8 10 0 0.3 0.6 0.9 1.2 V_{GS}-Gate-to-Source Voltage(V) V_{SD}-Source-to-Drain Voltage(V)

Fig.5 On-Resistance Variation with $V_{\mbox{\scriptsize GS}}$

Fig.6 Body Diode Characteristics

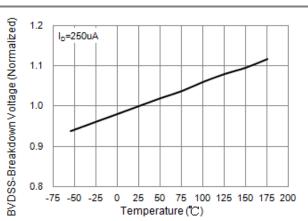
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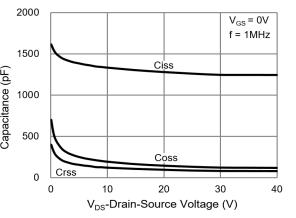
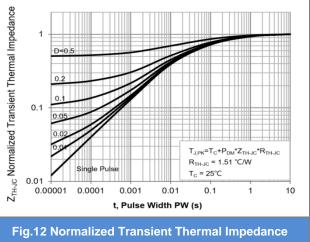


Fig.10 Capacitance vs. Drain-Source Voltage



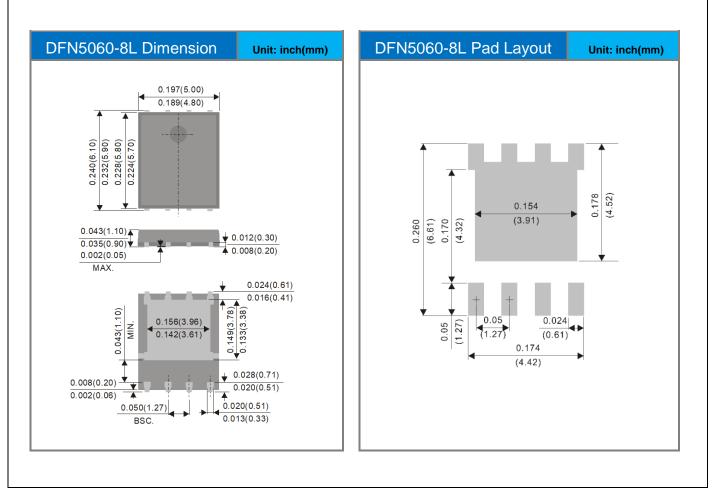




Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type Marking		Version
PJQ5442-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5442	Halogen free

Packaging Information & Mounting Pad Layout





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